TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74HC652AP

### OCTAL BUS TRANSCEIVER / REGISTER (3-STATE)

The TC74HC652A is high speed CMOS OCTAL BUS TRANSCEIVER/REGISTER fabricated with silicon gate CMOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

When the enable input GAB and  $\overline{GBA}$  are held high, the A1 thru A8 become inputs and the B1 thru B8 become outputs. When the GAB and  $\overline{\text{GBA}}$  are held low, the A1 thru A8 become output and the B1 thru B8 become inputs. When GAB is low and GBA is high, the outputs functions of the A and B Busses are disabled.

The select inputs (SAB, SBA) can multiplex stort and realtime (transparent mode) data.

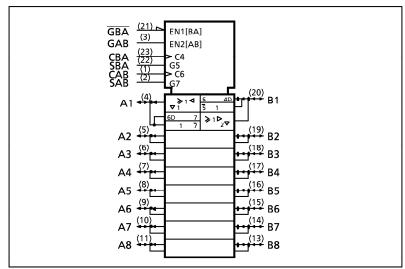
Data on the A Bus or B Bus can be clocked into the registers on the positive going transition of either CAB or CBA clock inputs, respectively.

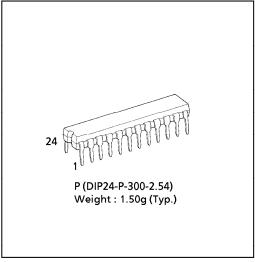
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

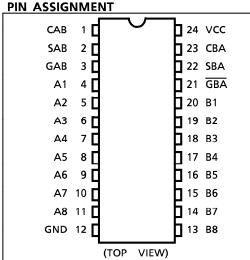
#### ${f FEATURES}$ :

- High Speed------f<sub>MAX</sub> = 73MHz (typ.) at  $V_{CC} = 5V$ • Low Power Dissipation  $I_{CC} = 4\mu A(Max.)$  at  $Ta = 25^{\circ}C$  • High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.) • Output Drive Capability 15 LSTTL Loads
- Symmetrical Output Impedance··· | I<sub>OH</sub> | = I<sub>OL</sub> = 6mA (Min.)
- Balanced Propagation Delays ····· t<sub>pLH</sub> ≃ t<sub>pHL</sub>
   Wide Operating Voltage Range ···· V<sub>CC</sub> (opr.) = 2V ~ 6V
- Pin and Function Compatible with 74LS652

#### IEC LOGIC SYSTEMBOL







#### APPLICATION NOTES

- 1) Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
- 2) All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

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#### TRUTH TABLE

GAB	GBA	CAB	СВА	SAB	SBA	Α	В	Function
	н	X*	X*	х	х	INPUTS Z	INPUTS Z	The output functions of A and B Busses are disabled.
	С	5	_	x	X	х	х	Both A and B Busses are used as inputs to the internal flip-flops. Data on the Bus will be stored on the rising edge of the Clock.
		X*	X *	x	L	OUTPUTS L H	INPUTS L H	The data on the B bus are displayed on the A bus.
L	L	X *		х	L	L	L	The data on the B Bus are displayed on the A Bus, and are stored into the B storage flip-flops on the rising edge of CBA.
		X*	X *	Х	Н	Qn	х	The data in the B storage flip-flops are displayed on the A Bus.
		X *	上	x	Н	LH	I	The data on the B Bus are stored into the B storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A Bus.
		X*	X*	L	×	INPUTS L H	OUTPUTS L H	The data on the A bus are displayed on the B bus.
			X*	L	х	L H	L	The data on the A Bus are displayed on the B Bus, and are stored into the A storage flip-flops on the rising edge of CAB.
H	Н	X *	X*	Н	х	x	Qn	The data in the A storage flip-flops are displayed on the B Bus.
			X*	Н	x	L H	L	The data on the A Bus are stored into the A storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B Bus.
Н	L	X *	X *	Н	I	OUTPUTS Qn	OUTPUTS Qn	The data in the A storage flip-flops are displayed on the B Bus, and the data in the B storage flip-flops are displayed onthe A

Notes: X: Don't Care

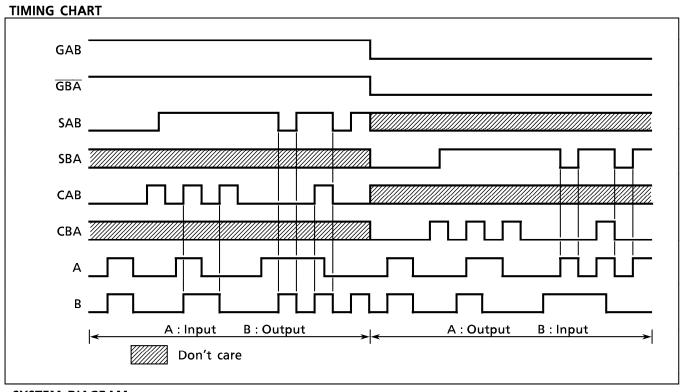
Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

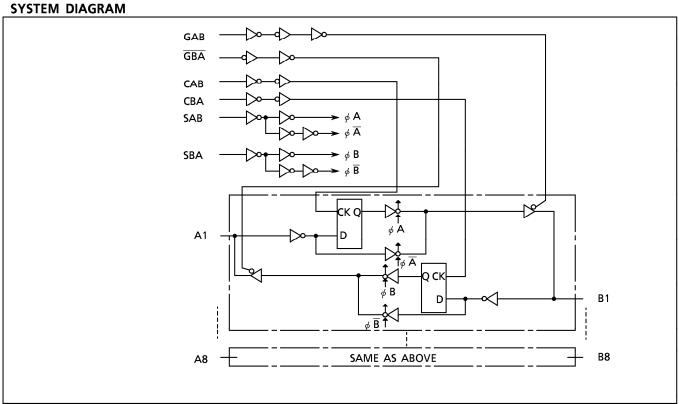
Z: High Impedance

\* The clocks are not internally gated with either Output Enable or Select Inputs. Therefore, data on the A and/or B Busses may be clocked into the storage flip-flops at any time.

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#### **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	<b>−</b> 0.5~7	V
DC Input Voltage	VIN	$-0.5 \sim V_{CC} + 0.5$	٧
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	٧
Input Diode Current	I <sub>IK</sub>	± 20	mA
Output Diode Current	I <sub>OK</sub>	±20	mA
DC Output Current	I <sub>OUT</sub>	±35	mA
DC V <sub>CC</sub> / Ground Current	I <sub>cc</sub>	± 75	mA
Power Dissipation	P <sub>D</sub>	500 (DIP)*	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

\*500mW in the range of Ta =  $-40^{\circ}\text{C}\sim65^{\circ}\text{C}$ . From Ta =  $65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  shall be applied until 300mW.

#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>CC</sub>	2~6	V
Input Voltage	V <sub>IN</sub>	0∼V <sub>CC</sub>	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	$0 \sim 1000 \text{ (V}_{CC} = 2.0\text{V)}$ $0 \sim 500 \text{ (V}_{CC} = 4.5\text{V)}$ $0 \sim 400 \text{ (V}_{CC} = 6.0\text{V)}$	ns

#### DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = -4	UNIT	
PARAIVIETER	STIVIBOL				MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High - Level Input Voltage					_ 		1.50 3.15 4.20	=	V	
Low - Level Input Voltage	VIL			2.0 4.5 6.0			0.50 1.35 1.80	=	0.50 1.35 1.80	V
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	=	1.9 4.4 5.9	=	V
Output voitage			$I_{OH} = -6 \text{ mA}$ $I_{OH} = -7.8 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	=	4.13 5.63	_	
Low - Level	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 20 \mu A$	2.0 4.5 6.0		0.0 0.0 0.0	0.1 0.1 0.1	=	0.1 0.1 0.1	v
Output Voltage	100		$I_{OL} = 6$ mA $I_{OL} = 7.8$ mA	4.5 6.0		0.17 0.18	0.26 0.26	_	0.33 0.33	
3 - State Output Off - State Current				6.0	_	_	±0.5	. –	± 5.0	
Input Leakage Current	I <sub>I N</sub>	$V_{IN} = V_{CC}$ or GND		6.0	_	_	± 0.1	_	± 1.0	μ <b>Α</b>
Quiescent Supply Current	I <sub>CC</sub>	$V_{IN} = V_{CC}$	or GND	6.0	_	_	4.0	_	40.0	

TIMING REQUIREMENTS (Input  $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST CONDITION		Ta =	25°C	Ta = − 40~85°C	UNIT
PARAIVIETER	STIVIBOL	TEST CONDITION	V <sub>CC</sub> (V)	TYP.	LIMIT	LIMIT	UNIT
Minimum Pulse Width (CK)	t <sub>W(L)</sub> t <sub>W(H)</sub>		2.0 4.5 6.0	_ _ _	75 15 13	95 19 16	
Minimum Set-up Time	ts		2.0 4.5 6.0	_ _ _	50 10 9	65 13 11	ns
Minimum Hold Time	t <sub>h</sub>		2.0 4.5 6.0	_ _ _	5 5 5	5 5 5	
Clock Frequency	f		2.0 4.5 6.0	_ _ _	6 31 36	5 25 29	MHz

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$ )

	SYMBOL TEST CONDITION		CL	1/	-	Γa = 25°0	-	Ta = − 40~85°C		UNIT
PARAMETER	STIVIBOL	TEST CONDITION	(pF)	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	OIVII
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>		50	2.0 4.5 6.0		25 7 6	60 12 10		75 15 13	
Propagation Delay Time	t <sub>pLH</sub>		50	2.0 4.5 6.0	<b>—</b>	74 21 18	150 30 26	_ _ _	190 38 32	
(BUS—BUS)	t <sub>pHL</sub>		150	2.0 4.5 6.0		91 26 22	190 38 32		240 48 41	
Propagation Delay Time	t <sub>pLH</sub>		50	2.0 4.5 6.0	_ _ _	98 28 24	210 42 36	_ _ _	265 53 45	ns
(CAB, CBA — BUS)	t <sub>pHL</sub>		150	2.0 4.5 6.0		116 33 28	250 50 43	_ 	315 63 54	115
Propagation Delay Time	t <sub>pLH</sub>		50	2.0 4.5 6.0		81 23 20	170 34 29		215 43 37	
(SAB, SBA — BUS)	t <sub>pHL</sub>		150	2.0 4.5 6.0		98 28 24	210 42 36	_ 	265 53 45	
Propagation Enable Time	t <sub>pZL</sub>		50	2.0 4.5 6.0		74 21 18	175 35 30		220 44 37	
(GAB, <del>GBA</del> – BUS)	t <sub>pZH</sub>	$R_L = 1k\Omega$	150	2.0 4.5 6.0	_ _ _	91 26 22	215 43 37	_ _ _	270 54 46	
Output Disa <u>ble t</u> ime (GAB, GBA — BUS)	t <sub>pLZ</sub> t <sub>pHZ</sub>	$R_L = 1k\Omega$	50	2.0 4.5 6.0	_ _ _	50 21 18	175 35 30	_ _ _	220 44 37	

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$ ) (Cont'd)

• • • •											
	CVMDOL	TEST CONDITION			Т	a = 25°0	<b>.</b>	Ta = - 4	LINIT		
PARAMETER	SAIMBOL	TEST CONDITION	CL (pF)	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.		
				2.0	6	19	_	5	_		
Maximum Clock Frequency	f <sub>MAX</sub>		50	4.5	31 36	67 79	_	25 29	-	MHz	
				6.0	36	/9	_	29	_		
Input Capacitance	C <sub>IN</sub>				_	5	10	_	10		
Output Capacitance	C <sub>OUT</sub>				_	13	_	_	_	pF	
Power Dissipation Capacitance	C <sub>PD</sub> (1)				_	39	_	_	_		

Note CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$  (per bit)

## DIP 24PIN OUTLINE DRAWING (DIP24-P-300-2.54)

Unit in mm

